

Description

The SI2309 is the high cell density trenched P-ch MOSFETs, which provides excellent RDSON and efficiency for most of the small power switching and load switch applications.

The SI2309 meet the RoHS and Green Productrequirement with full function reliability approved.

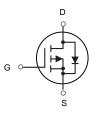


General Features

 $V_{DS} = -60V, I_{D} = -2A$

 $R_{DS(ON)}$ <200m Ω @ V_{GS} =-10V

 $R_{DS(ON)}$ <300m Ω @ V_{GS} =-4.5V



Application

Load switch

PWM application

P-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
SI2309	SOT-23	HXY MOSFET	3000

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Limit	Unit
V _{DS}	Drain-Source Voltage	-60	V
V _G s	Gate-Source Voltage	±20	V
I _D	Drain Current-Continuous	-2	Α
Ірм	Drain Current-Pulsed (Note 1)	-5.2	А
P _D	Maximum Power Dissipation	1	W
Т,,Тѕтс	Operating Junction and Storage Temperature Range	-55 To 150	°C
Reja	Thermal Resistance, Junction-to-Ambient (Note 2)	83.3	°C/W



Electrical Characteristics (T_C=25°C unless otherwise noted)

Symbol	Parameter	Condition	Min	Тур	Max	Unit
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	Vgs=0V lp=-250µA	-60			V
I _{DSS}	Zero Gate Voltage Drain Current(T _A =25°C) V _{DS} =-60V, V _{GS} =0V				-1	μA
	Zero Gate Voltage Drain Current(T _A =125°C) V _{DS} =-60V, V _{GS} =0V				-100	uA
I _{GSS}	Gate-Body Leakage Current	Vgs=±20V, Vds=0V			±100	nA
$V_{\rm GS(TH)}$	Gate Threshold Voltage	VDS=VGS, ID=-250μA	-1.0	-1.5	-2.5	V
R _{DS(ON)}	Drain-Source On-State Resistance②	Vgs=-10V, ID=-2A		160	200	mΩ
R _{DS(ON)}	Drain-Source On-State Resistance②	Vgs=-4.5V, ID=-1A		200	300	mΩ
C _{iss}	Input Capacitance			310		pF
C _{oss}	Output Capacitance	V _{DS} =-30V, V _{GS} =0V, f=1MHz		22		pF
C _{rss}	Reverse Transfer Capacitance			15		pF
Q_g	Total Gate Charge	VDS=-30V ID=-2A,		5.4		nC
Q_{gs}	Gate Source Charge			1.1		nC
Q_{gd}	Gate Drain Charge	Vgs=-10V		1.6		nC
t _{d(on)}	Turn on Delay Time	V 00V		41		ns
t _r	Turn on Rise Time	VDD=-30V, ID=-2A,		22		ns
t _{d(off)}	Turn Off Delay Time	R _G =3.3Ω, V _G S=-10V	_	25		ns
t _f	Turn Off Fall Time	V50- 10 V		32		ns
I _{SD}	Source drain current(Body Diode)	T _A =25°C			-2.0	А
V _{SD}	Forward on voltage②	Tj=25℃, IsD=-2A, Vgs=0V		-0.84	-1.2	V

Notes:

① Pulse width limited by maximum allowable junction temperature

②Pulse test ; Pulse width≤300μs, duty cycle≤2%.



Typical Electrical and Thermal Characteristics (Curves)

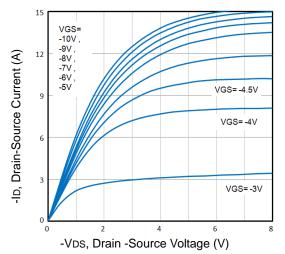


Fig1. Typical Output Characteristics

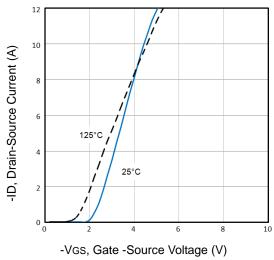


Fig3. Typical Transfer Characteristics

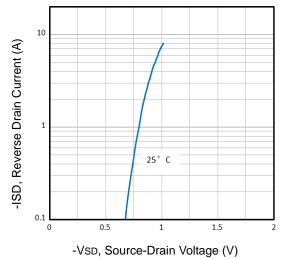


Fig5. Typical Source-Drain Diode Forward Voltage

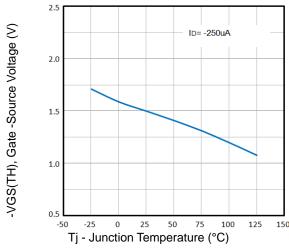


Fig2. Normalized Threshold Voltage Vs. Temperature

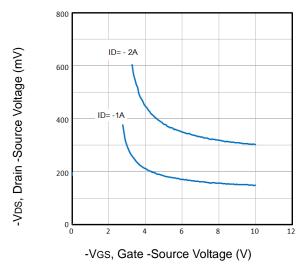


Fig4. Drain -Source Voltage vs Gate -Source Voltage

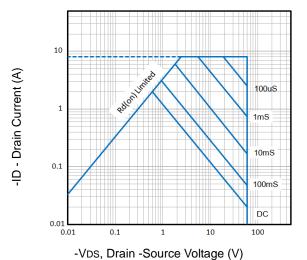


Fig6. Maximum Safe Operating Area

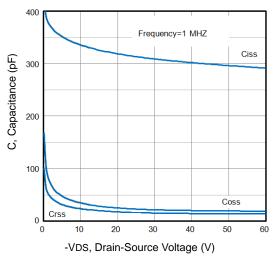


Fig7. Typical Capacitance Vs. Drain-Source Voltage

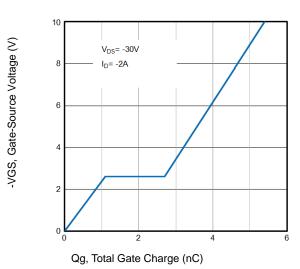


Fig8. Typical Gate Charge Vs. Gate-Source Voltage

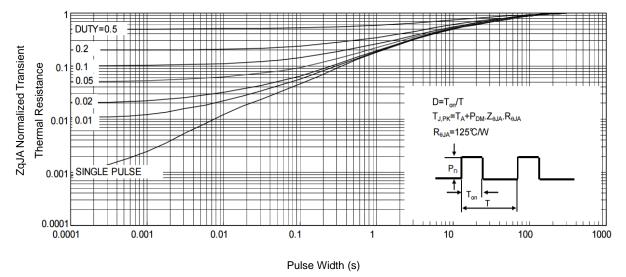


Fig9. Normalized Maximum Transient Thermal Impedance

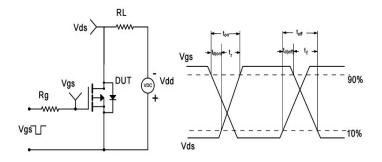
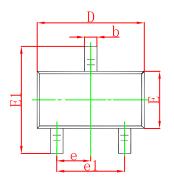
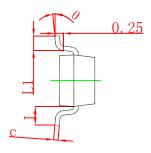


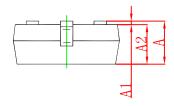
Fig10. Switching Time Test Circuit and waveforms



SOT-23 Package Outline Dimensions

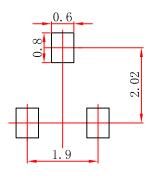






Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950 TYP		0.037 TYP		
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

SOT-23 Suggested Pad Layout



- Note: 1.Controlling dimension: in millimeters.
- 2.General tolerance:± 0.05mm.
 3.The pad layout is for reference purposes only.



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